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Kind regards,

Team Nexperia

PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

Rev. 10 — 21 December 2011

Product data sheet

1. Product profile

1.1 General description

PNP Resistor-Equipped Transistor (RET) family in small Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number	Package			NPN	Package	
	NXP JEITA JEDEC complement		configuration			
PDTA114EE	SOT416	SC-75	-	PDTC114EE	ultra small	
PDTA114EM	SOT883	SC-101	-	PDTC114EM	leadless ultra small	
PDTA114ET	SOT23	-	TO-236AB	PDTC114ET	small	
PDTA114EU	SOT323	SC-70	-	PDTC114EU	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Digital application in automotive and industrial segments
- Control of IC inputs

- Cost-saving alternative for BC847/857 series in digital applications
- Switching loads

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		0.8	1.0	1.2	



2. Pinning information

Table 3. Pinning

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
SOT23; S	SOT323; SOT416		
1	input (base)		
2	GND (emitter)	[3]	R1 3
3	output (collector)		1 R2 2 sym003
SOT883			
1	input (base)		
2	GND (emitter)	1 3	3
3	output (collector)	2 Transparent top view	1 R1 R2 2 sym003

3. Ordering information

Table 4. Ordering information

Type number	Package					
	Name	Description	Version			
PDTA114EE	SC-75	plastic surface-mounted package; 3 leads	SOT416			
PDTA114EM	SC-101	leadless ultra small plastic package; 3 solder lands; body 1.0 \times 0.6 \times 0.5 mm	SOT883			
PDTA114ET	-	plastic surface-mounted package; 3 leads	SOT23			
PDTA114EU	SC-70	plastic surface-mounted package; 3 leads	SOT323			

4. Marking

Table 5. Marking codes

Type number	Marking code[1]
PDTA114EE	03
PDTA114EM	E5
PDTA114ET	*03
PDTA114EU	*03

^{[1] * =} placeholder for manufacturing site code.

5. Limiting values

Table 6. Limiting values

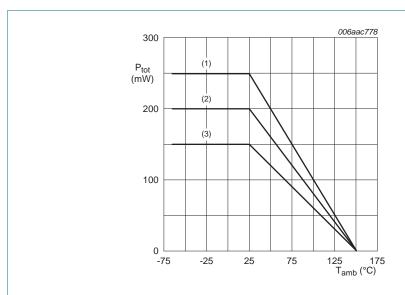
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V_{EBO}	emitter-base voltage	open collector		-	-10	V
VI	input voltage					
	positive			-	+40	V
	negative			-	-10	V
I _O	output current			-	-100	mΑ
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$				
	PDTA114EE (SOT416)		[1][2]	-	150	mW
	PDTA114EM (SOT883)		[2][3]	-	250	mW
	PDTA114ET (SOT23)		<u>[1]</u>	-	250	mW
	PDTA114EU (SOT323)		<u>[1]</u>	-	200	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	+150	°C
T _{stg}	storage temperature			-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

^[3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.



- SOT23; FR4 PCB, standard footprint
 SOT883; FR4 PCB with 70 μm copper strip line, standard footprint
- (2) SOT323; FR4 PCB, standard footprint
- (3) SOT416; FR4 PCB, standard footprint

Fig 1. Power derating curves

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PDTA114EE (SOT416)		[1][2]	-	830	K/W
	PDTA114EM (SOT883)		[2][3]	-	500	K/W
	PDTA114ET (SOT23)		<u>[1]</u> _	-	500	K/W
	PDTA114EU (SOT323)		<u>[1]</u> _	-	625	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.
- [3] Device mounted on an FR4 PCB with 70 μm copper strip line, standard footprint.

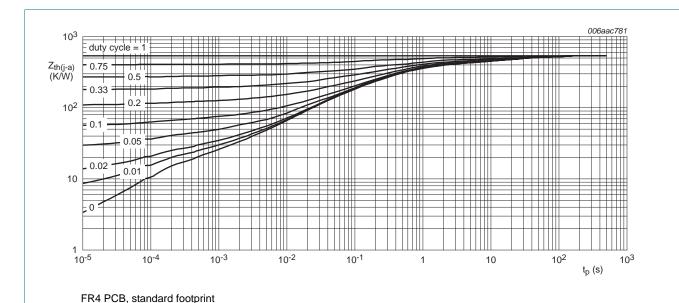
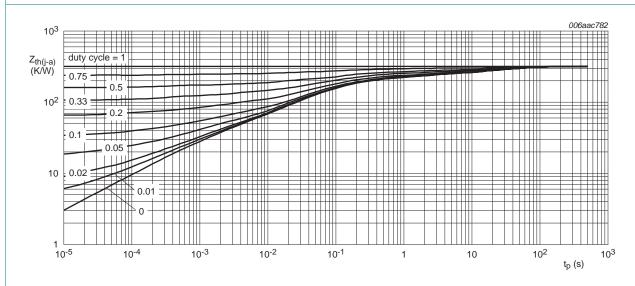


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EE (SOT416); typical values



FR4 PCB, 70 µm copper strip line

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EM (SOT883); typical values

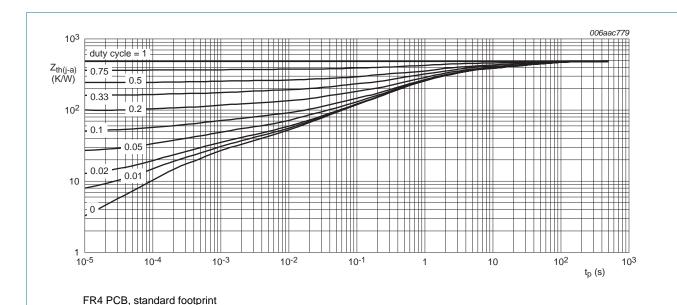


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114ET (SOT23); typical values

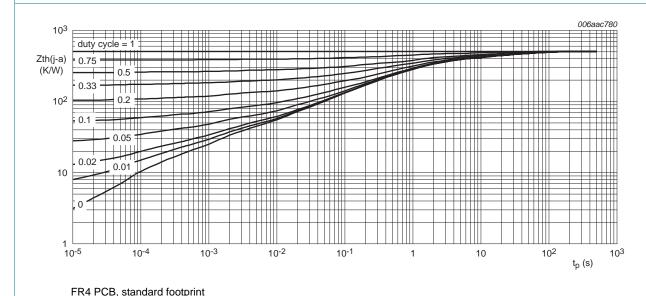


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for PDTA114EU (SOT323); typical values

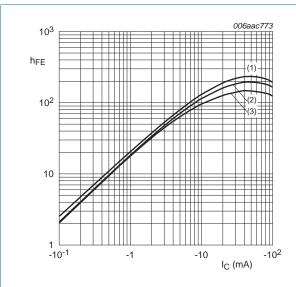
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

Parameter collector-base	Conditions	Min	Тур	Max	Unit
collector-base					
cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
collector-emitter	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A}$	-	-	-1	μА
cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	-5	μΑ
emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-400	μΑ
DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -5 \text{ mA}$	30	-	-	
collector-emitter saturation voltage	$I_C = -10 \text{ mA};$ $I_B = -0.5 \text{ mA}$	-	-	-150	mV
off-state input voltage	$V_{CE} = -5 \text{ V};$ $I_{C} = -100 \mu\text{A}$	-	-1.1	-0.8	V
on-state input voltage	$V_{CE} = -0.3 \text{ V};$ $I_{C} = -10 \text{ mA}$	-2.5	-1.8	-	V
bias resistor 1 (input)		7	10	13	$k\Omega$
bias resistor ratio		0.8	1.0	1.2	
collector capacitance	$V_{CB} = -10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$	-	-	3	pF
transition frequency	$V_{CE} = -5 \text{ V};$ $I_{C} = -10 \text{ mA};$ f = 100 MHz	[1] -	180	-	MHz
	cut-off current DC current gain collector-emitter saturation voltage off-state input voltage on-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance	$\begin{array}{c} \text{VCE} = -30 \text{ V}, \text{ IB} = 0 \text{ A}, \\ T_j = 150 \text{ °C} \\ \\ \text{emitter-base} \\ \text{cut-off current} \\ \\ \text{DC current gain} \\ \\ \text{Collector-emitter} \\ \text{saturation voltage} \\ \\ \text{I}_C = -10 \text{ mA}; \\ \\ \text{I}_B = -0.5 \text{ mA} \\ \\ \text{off-state input} \\ \text{voltage} \\ \\ \text{I}_C = -100 \mu \text{A} \\ \\ \text{on-state input} \\ \text{voltage} \\ \\ \text{I}_C = -100 \mu \text{A} \\ \\ \text{on-state input} \\ \text{voltage} \\ \\ \text{I}_C = -10 \text{ mA} \\ \\ \text{bias resistor 1 (input)} \\ \\ \text{bias resistor ratio} \\ \\ \text{collector capacitance} \\ \\ \text{VCB} = -10 \text{ V}; \\ \\ \text{I}_C = -10 \text{ mA}; \\ \\ \text{transition frequency} \\ \\ \text{VCE} = -5 \text{ V}; \\ \\ \text{I}_C = -10 \text{ mA}; \\ \\ \\ \text{I}_C = -10 \text{ mA}; \\ \\ \\ \text{I}_C = -10 \text{ mA}; \\ \\ \\ \\ \text{I}_C = -10 \text{ mA}; \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	$V_{CE} = -30 \text{ V}, \ I_B = 0 \text{ A}, \\ T_j = 150 \text{ °C}$ $\text{emitter-base} \\ \text{cut-off current}$ $V_{EB} = -5 \text{ V}; \ I_C = 0 \text{ A}$ $\text{collector-emitter} \\ \text{saturation voltage} \qquad I_C = -10 \text{ mA}; \\ I_B = -0.5 \text{ mA}$ $\text{off-state input} \\ \text{voltage} \qquad V_{CE} = -5 \text{ V}; \\ I_C = -100 \text{ \muA}$ $\text{on-state input} \\ \text{voltage} \qquad V_{CE} = -0.3 \text{ V}; \\ I_C = -10 \text{ mA}$ $\text{bias resistor 1 (input)} \qquad 7$ $\text{bias resistor ratio} \qquad 0.8$ $\text{collector capacitance} \qquad V_{CB} = -10 \text{ V}; \\ I_E = i_e = 0 \text{ A}; \text{ f} = 1 \text{ MHz}$ $\text{transition frequency} \qquad V_{CE} = -5 \text{ V}; \\ I_C = -10 \text{ mA}; \qquad I_C = -10 \text{ mA};$	emitter-base cut-off current $V_{EB} = -5 \text{ V}; \ I_{C} = 0 \text{ A} \qquad - \qquad -$ collector-emitter saturation voltage $I_{C} = -10 \text{ mA}; \qquad - \qquad -$ collector-emitter $I_{C} = -10 \text{ mA}; \qquad - \qquad -$ collector-emitter $I_{B} = -0.5 \text{ mA} \qquad 0 \qquad -$ collector-emitter $I_{B} = -0.5 \text{ mA} \qquad -$ off-state input $V_{CE} = -5 \text{ V}; \qquad - \qquad -1.1$ voltage $I_{C} = -100 \text{ \muA} \qquad -$ on-state input $V_{CE} = -0.3 \text{ V}; \qquad -2.5 \qquad -1.8$ voltage $I_{C} = -10 \text{ mA} \qquad -$ bias resistor 1 (input) $I_{C} = -10 \text{ mA} \qquad -$ to collector capacitance $V_{CB} = -10 \text{ V}; \qquad -$ collector capacitance $V_{CB} = -10 \text{ V}; \qquad -$ collector capacitance $V_{CB} = -10 \text{ V}; \qquad -$ collector capacitance $V_{CB} = -10 \text{ V}; \qquad -$ collector capacitance $V_{CB} = -5 \text{ V}; \qquad -$ 110 collector capacitance $V_{CB} = -10 \text{ V}; \qquad -$ coll	$\begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Characteristics of built-in transistor.



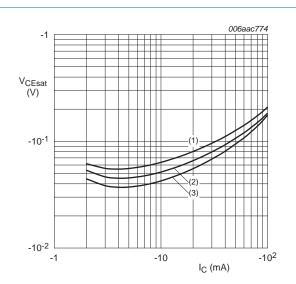
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 6. DC current gain as a function of collector current; typical values



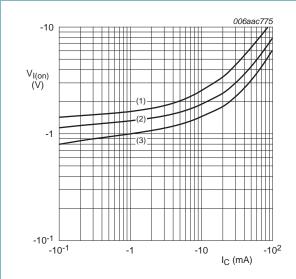
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 7. Collector-emitter saturation voltage as a function of collector current; typical values

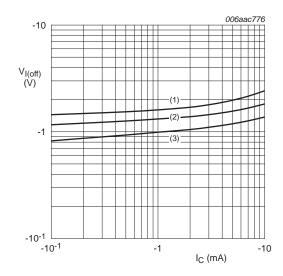


$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 8. On-state input voltage as a function of collector current; typical values



$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Fig 9. Off-state input voltage as a function of collector current; typical values

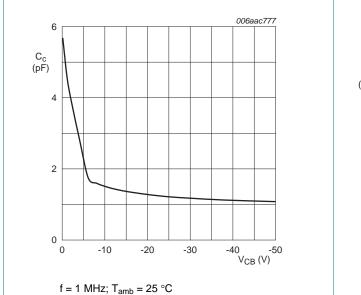


Fig 10. Collector capacitance as a function of collector-base voltage; typical values

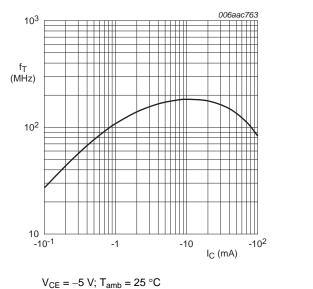


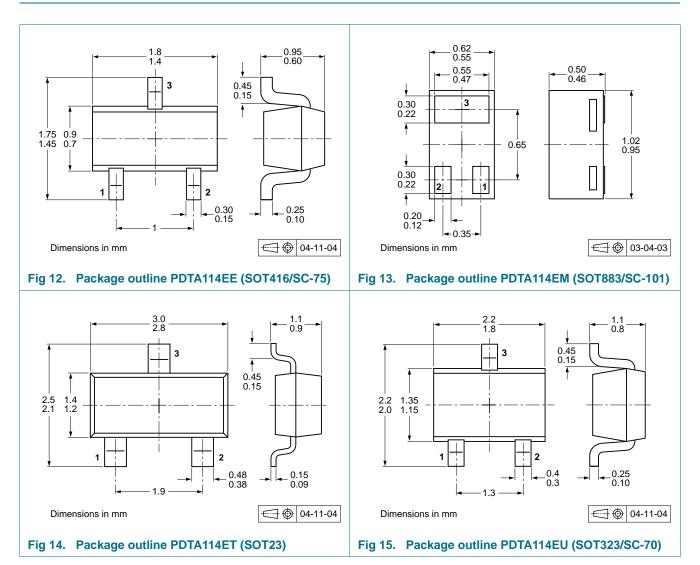
Fig 11. Transition frequency as a function of collector current; typical values of built-in transistor

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



10. Packing information

Table 9. Packing methods

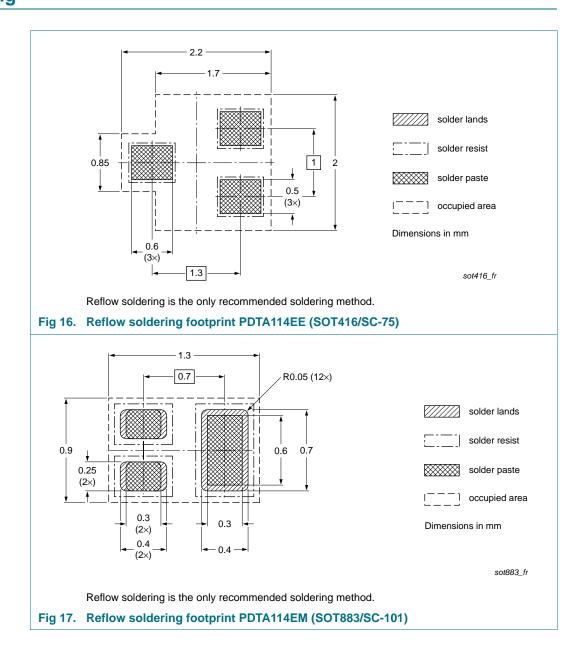
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

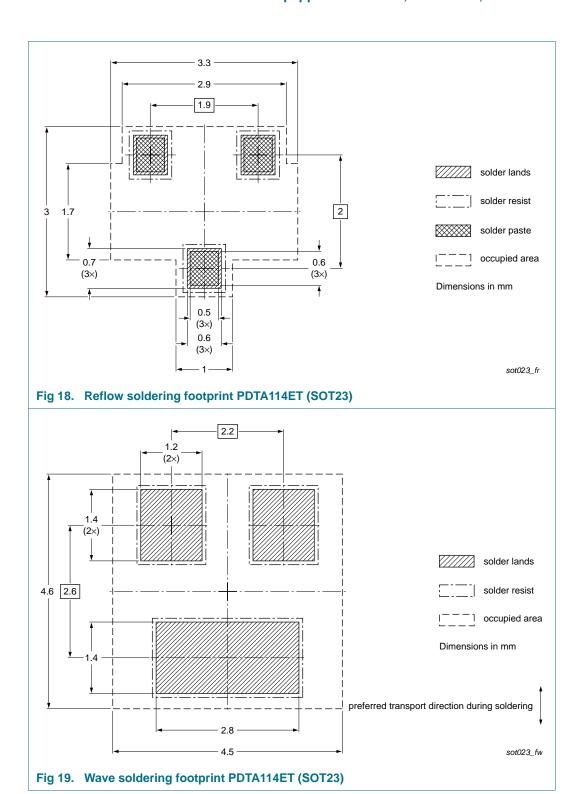
Type number	Package	age Description		Packing quantity		
			3000	10000		
PDTA114EE	SOT416	4 mm pitch, 8 mm tape and reel	-115	-135		
PDTA114EM	SOT883	2 mm pitch, 8 mm tape and reel	-	-315		
PDTA114ET	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235		
PDTA114EU	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135		

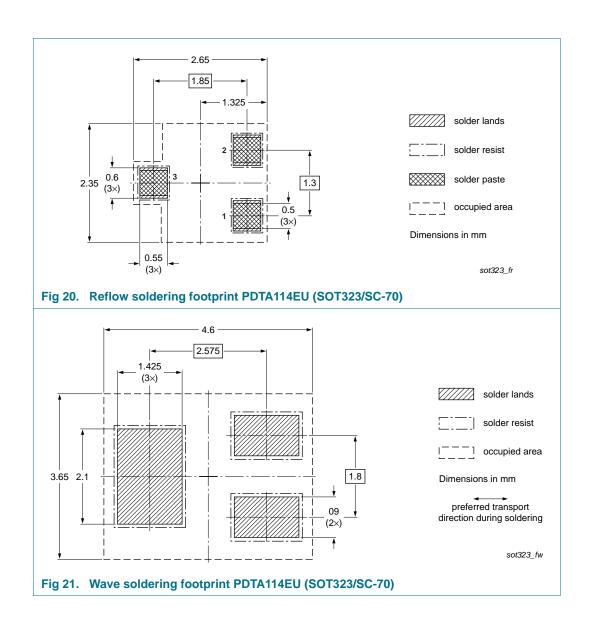
^[1] For further information and the availability of packing methods, see $\underline{\text{Section } 14}$.

PDTA114E_SER

11. Soldering







PNP resistor-equipped transistors; R1 = 10 kΩ, R2 = 10 kΩ

12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PDTA114E_SER v.10	20111221	Product data sheet	-	PDTA114E_SER v.9
Modifications:	• Figure 2 and	d <u>5</u> : corrected		
PDTA114E_SER v.9	20111122	Product data sheet	-	PDTA114E_SERIES v.8
PDTA114E_SERIES v.8	20040802	Product specification	-	PDTA114E_SERIES v.7
PDTA114E_SERIES v.7	20030410	Product specification	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PDTA114E_SER

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PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

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PDTA114E series

PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 10 k Ω

15. Contents

1	Product profile
1.1	General description 1
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data 1
2	Pinning information 2
3	Ordering information 2
4	Marking 2
5	Limiting values 3
6	Thermal characteristics 4
7	Characteristics 7
8	Test information 9
8.1	Quality information 9
9	Package outline
10	Packing information 10
11	Soldering 11
12	Revision history 14
13	Legal information
13.1	Data sheet status
13.2	Definitions
13.3	Disclaimers
13.4	Trademarks16
14	Contact information 16
15	Contents 17

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DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143ZF3T5G

NSBC114YF3T5G NSBC123TF3T5G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G RN1303(TE85L,F)

RN4605(TE85L,F) TTEPROTOTYPE79 DDTC114EUAQ-7-F EMH15T2R SMUN2214T3G SMUN5335DW1T1G NSBC114TF3T5G

NSBC143ZPDP6T5G NSVMUN5113DW1T3G SMUN5230DW1T1G SMUN5133T1G SMUN2214T1G DTC114EUA-TP

NSBA144EF3T5G NSVDTA114EET1G 2SC2223-T1B-A 2SC3912-TB-E SMUN5237DW1T1G SMUN5213DW1T1G

SMUN5114DW1T1G SMUN2111T1G NSVDTC144EM3T5G DTC124ECA-TP DTC123TM3T5G DTA114ECA-TP DTA113EM3T5G

DCX115EK-7-F DTC113EM3T5G NSVMUN5135DW1T1G NSVMUN2237T1G